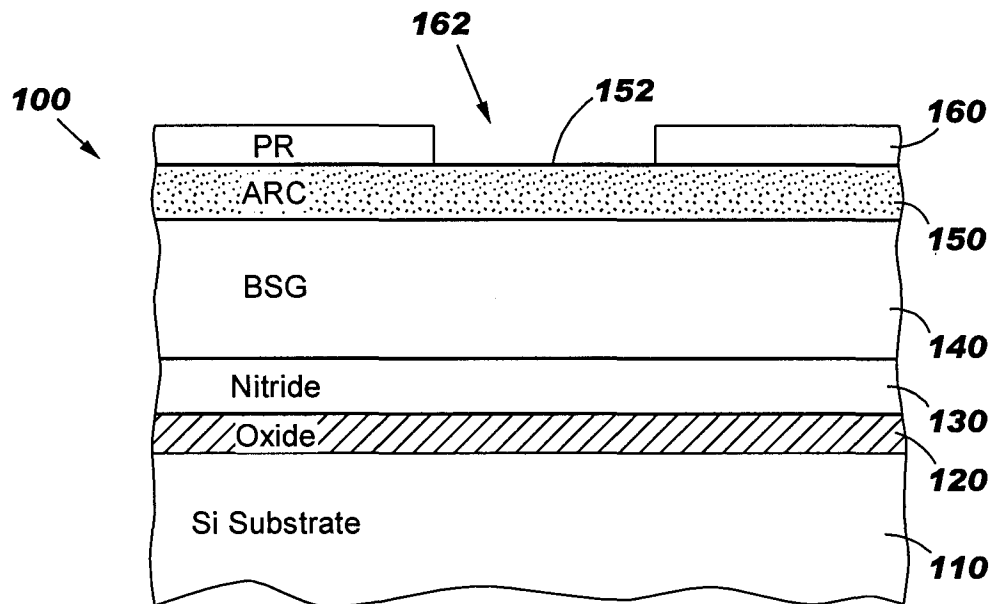


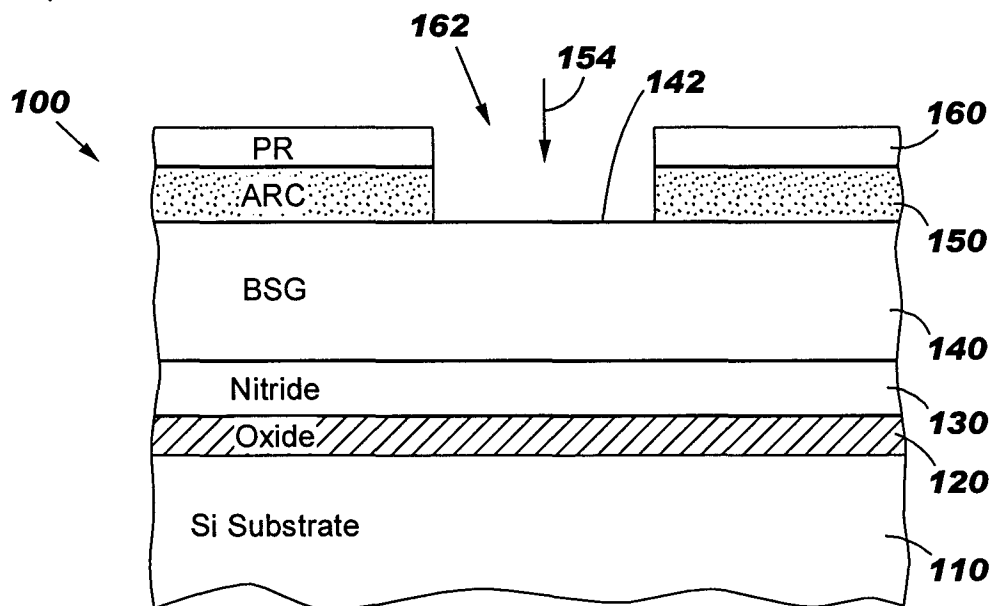
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FIG. 1B



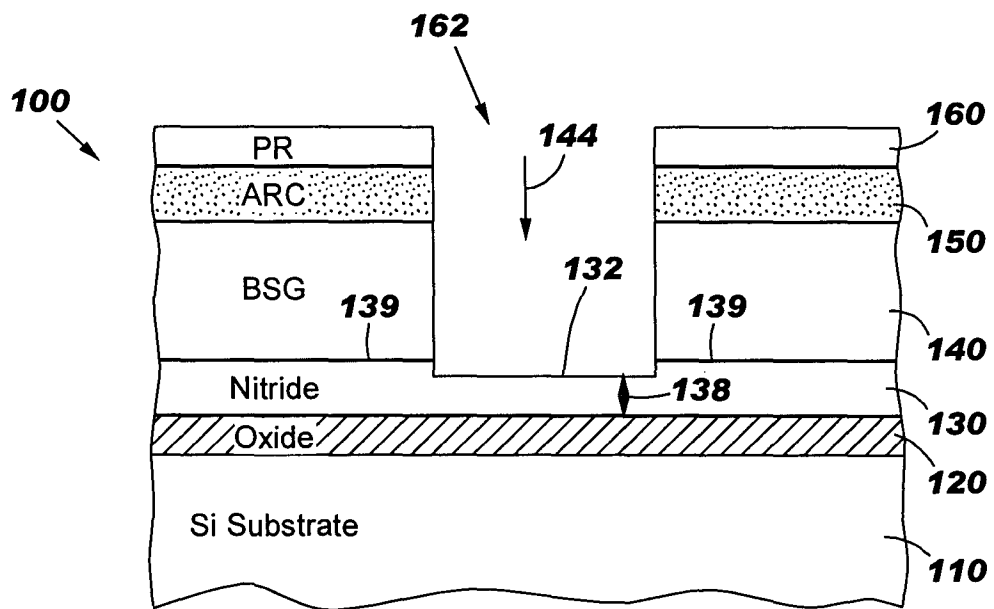
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FIG. 1C



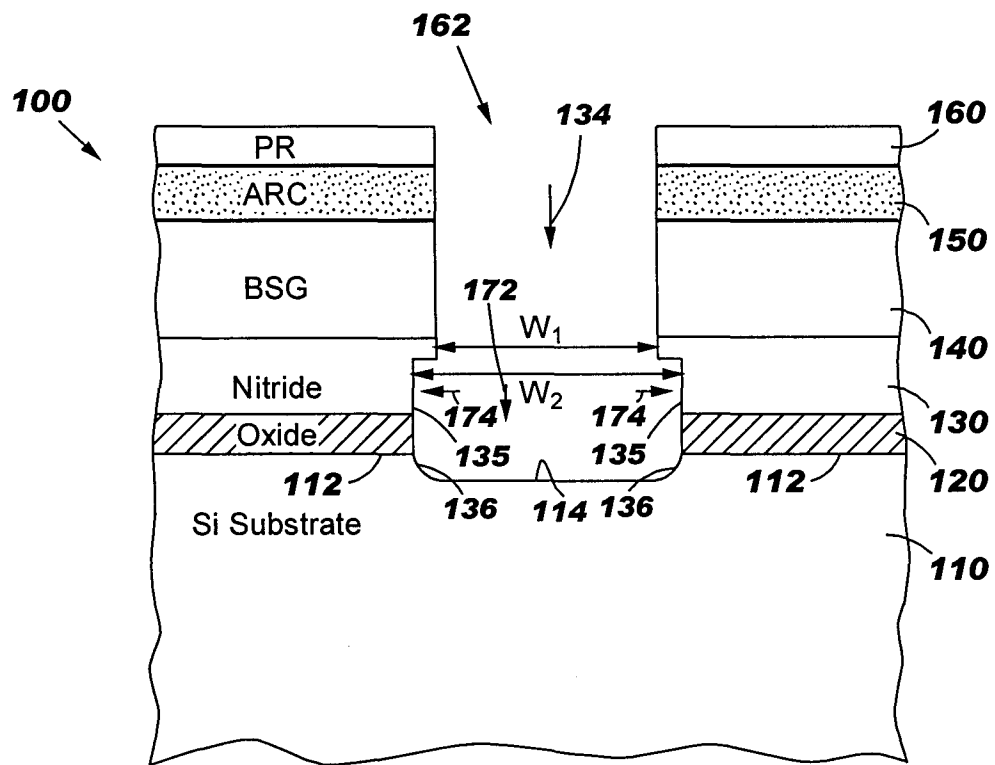
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FIG. 1D



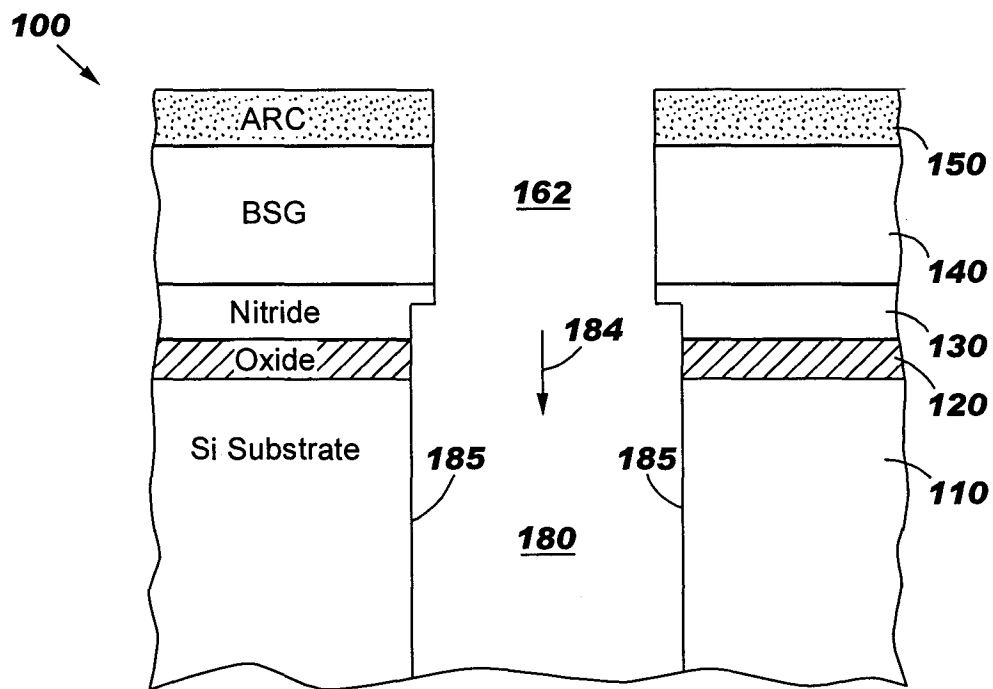
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FIG. 1E



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FIG. 1F



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FIG. 2

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Row	Column 1	Column 2	Column 3	Column 4	Column 5
1	Etching Parameters [Unit]	Etching through ARC layer	Etching through BSG layer	Etching through Silicon Nitride layer and pad oxide layer	De-polymerization
2	RF Power [W]	500	1,400	1,000	500
3	Time [sec]	80	330	35	20
4	Pressure [mT]	160	45	50	200
5	CO [sccm]	0	50	40	0
6	Ar [sccm]	500	200	0	100
7	C ₄ F ₈ [sccm]	0	10	0	0
8	O ₂ [sccm]	10	5	6	30
9	CH ₂ F ₂ [sccm]	20	0	20	0

